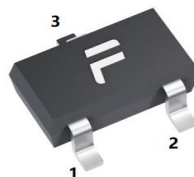
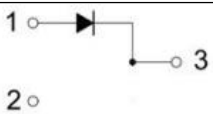
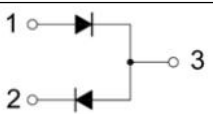
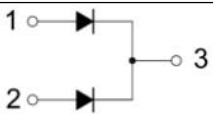
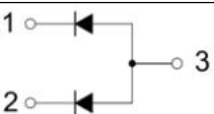


BAS40W/-04/-05/-06

SOT-323 Schottky Barrier Diode 肖特基势垒二极管



Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS40W	BAS40W-04	BAS40W-05	BAS40W-06
Pin 管脚				
Mark 打标	43.	44	45	46

Absolute Maximum Ratings 最大额定值

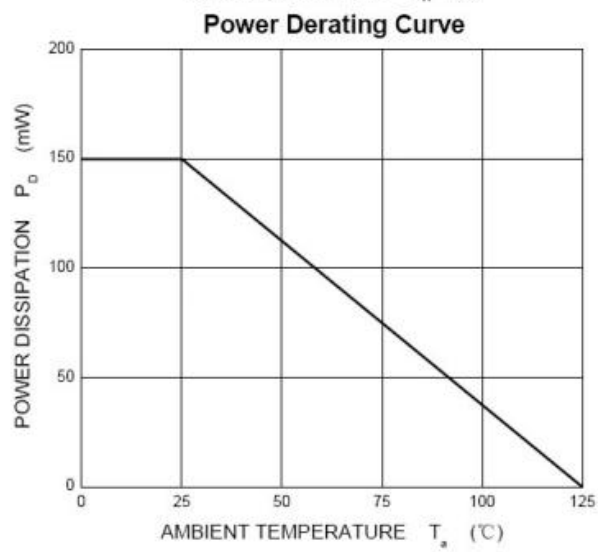
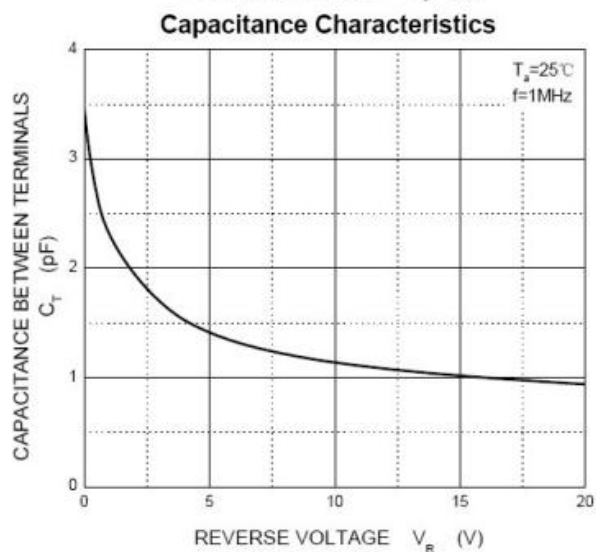
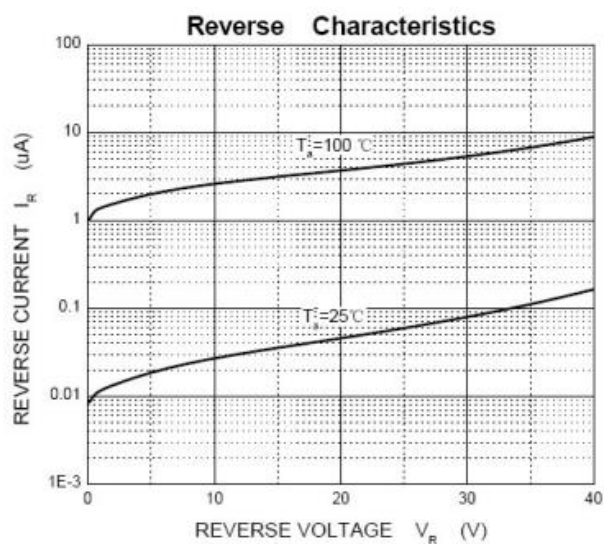
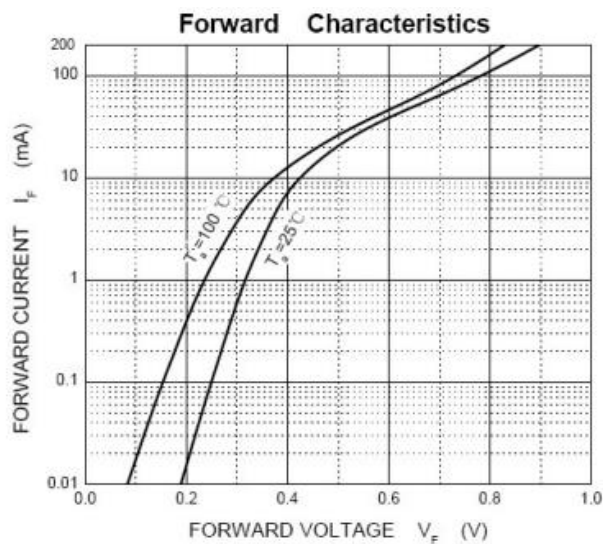
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	40	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Max Forward Work Current 最大正向工作电流	I_{FM}	200	mA
Power dissipation 耗散功率	$P_D(T_A=25^{\circ}C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-50to+150 $^{\circ}C$	

Electrical Characteristics 电特性

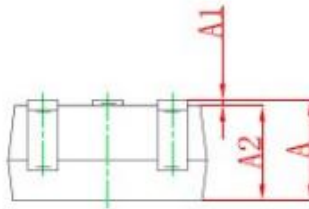
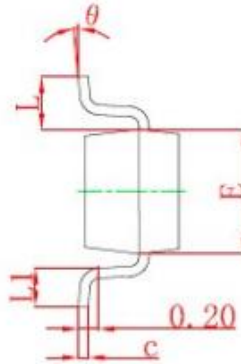
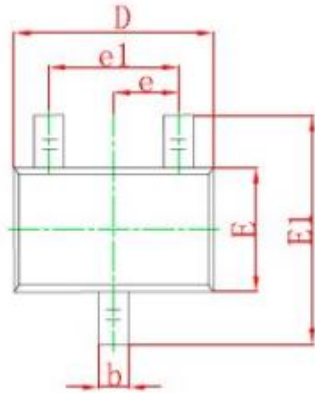
($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=10\mu A$)	$V_{(BR)}$	40	—	V
Reverse Leakage Current 反向漏电流($V_R=30V$)	I_R	—	200	nA
Forward Voltage($I_F=1mA$) 正向电压($I_F=40mA$)	V_F	—	0.38 1	V
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_D	—	5	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	5	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°